DDR Memory Errors Caused by Row Hammer

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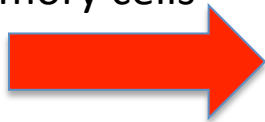
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Outline

- What is Row Hammer?
- What Research has been done?
  - CMU
  - Google Project Zero
  - Java Script
  - Third IO
- ECC
- Mitigation Strategies
- Software that creates Row Hammer
- Summary

What is Row Hammer?
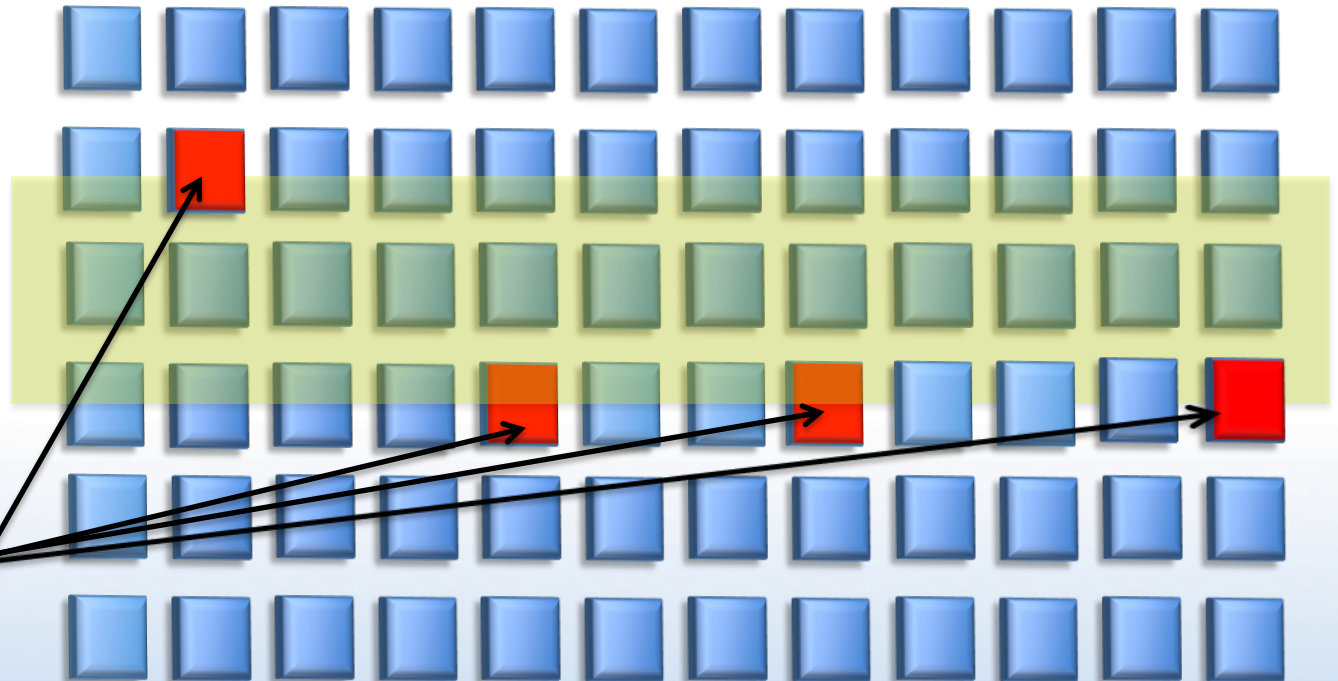
- Disturbance Errors: Row to Row Coupling

Excessive ACTIVATE commands apply repeated charge to the memory cells

Electromagnetic field induced by applied voltage

Cells lose charge by repeated nearby electromagnetic field, causing a coupled bit
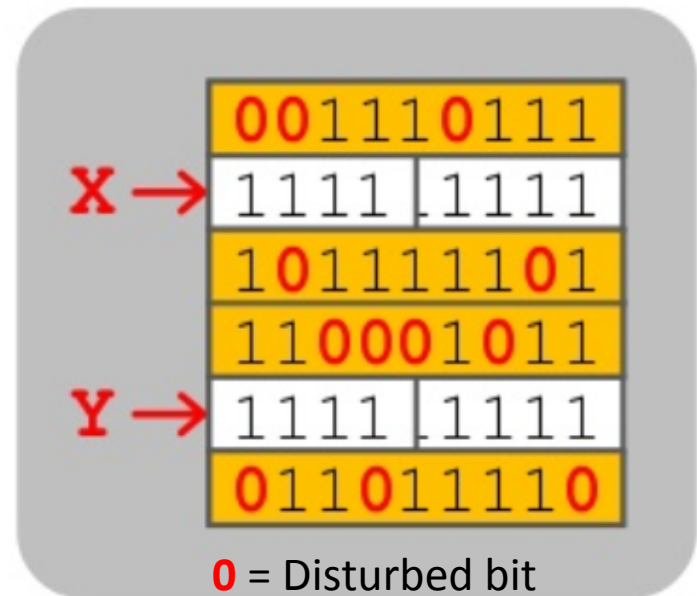
Source: http://www.eurosoft-uk.com/eurosoft-test-bulletin-testing-row-hammer/

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Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Yoongu Kim[1]   Ross Daly*   Jeremie Kim[1]   Chris Fallin*   Ji Hye Lee[1]
Donghyuk Lee[1]   Chris Wilkerson[2]   Konrad Lai   Onur Mutlu[1]

[1]Carnegie Mellon University   [2]Intel Labs

July 2014

```
loop:
  mov (X), %eax
  mov (Y), %ebx
  clflush (X)
  clflush (Y)
  mfence
  jmp loop
```
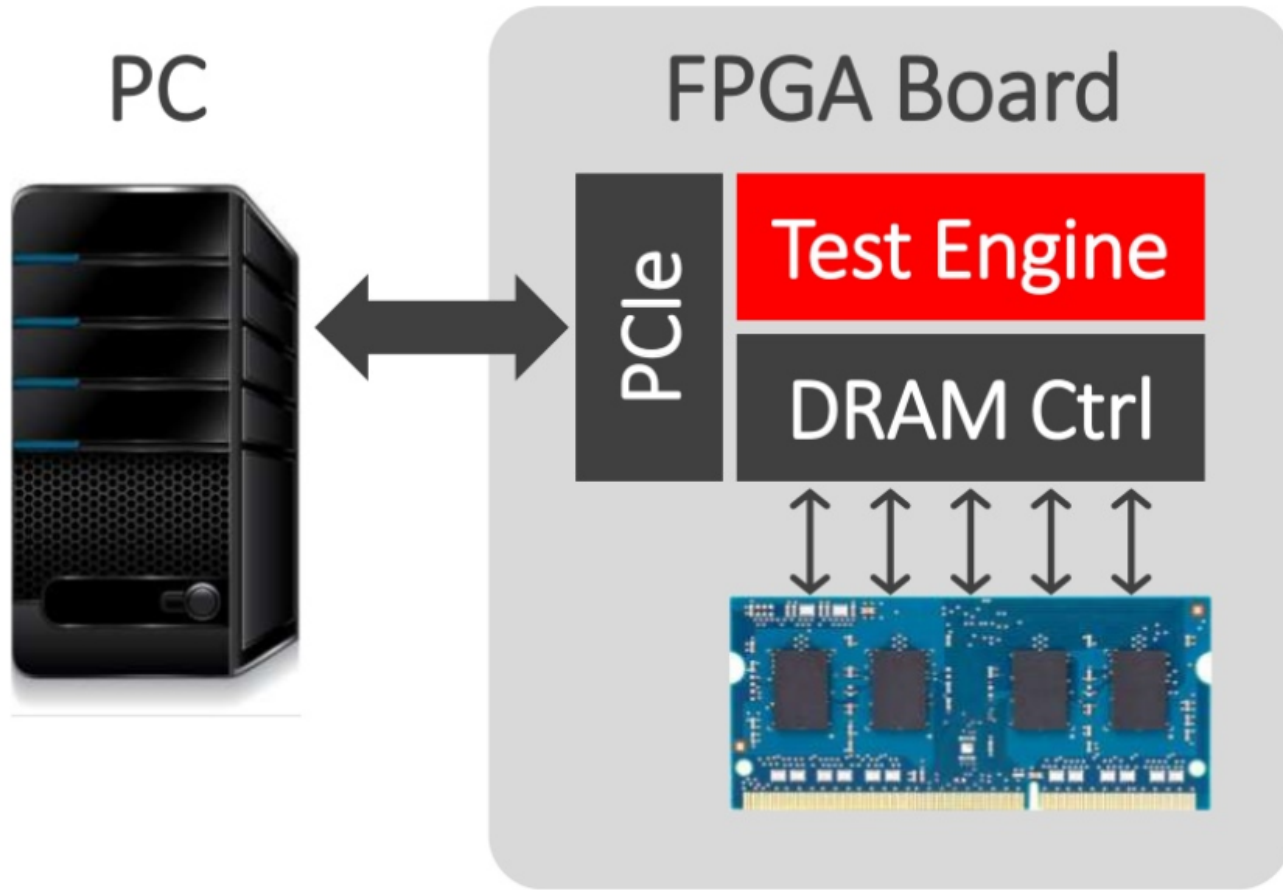

0 = Disturbed bit

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Security Implications

- Breach of memory protection
  - OS page (4KB) fits inside DRAM row (8KB)
  - Adjacent DRAM row is a different OS page
- Vulnerability: disturbance attack
  - By accessing its own page a program can corrupt pages belonging to another program
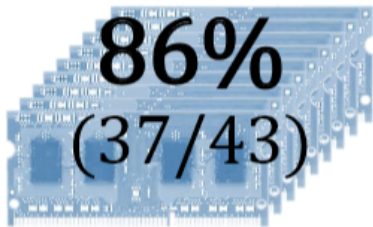
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CMU then induced errors with an FPGA based system

PC

FPGA Board

PCIe

Test Engine

DRAM Ctrl

Results

1. Most Modules Are at Risk

A company	B company	C company
86% (37/43)	**83%** (45/54)	**88%** (28/32)
Up to 1.0×10^7 errors	Up to 2.7×10^6 errors	Up to 3.3×10^5 errors

Source: https://users.ece.cmu.edu/~omutlu/pub/dram-row-hammer_kim_talk_isca14.pdf

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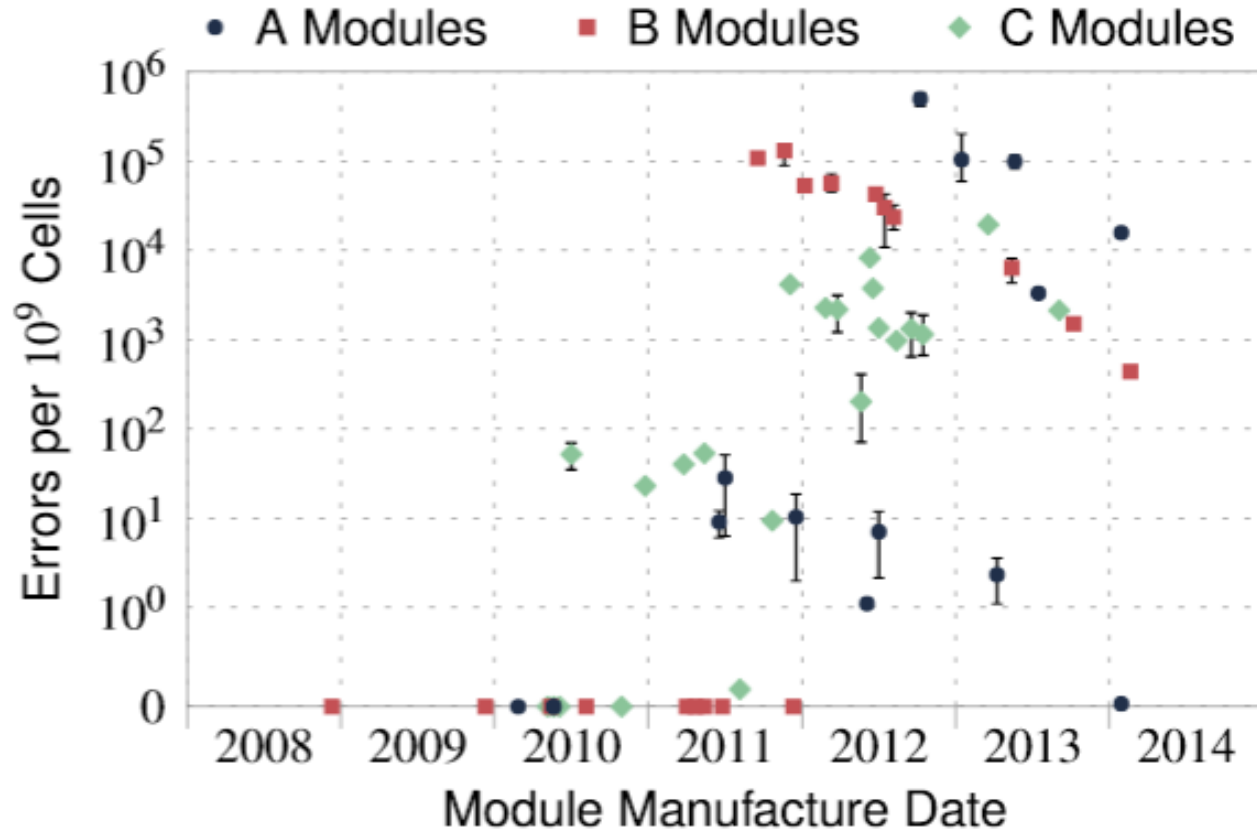*Power Tools for Bus Analysis*

How many errors did CMU find?

Figure 3. Normalized number of errors vs. manufacture date

Source: https://users.ece.cmu.edu/~omutlu/pub/dram-row-hammer_kim_talk_isca14.pdf

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CMU Study Summary

- Temperature did not play a role in bit flips
- *"Disturbance errors are widespread in DRAM chips sold and used today"*
- *"Due to difficulties in DRAM scaling, new and unexpected types of failures may appear"*
- *Recommends a mitigation strategy of ACT or REF adjacent rows when accesses are made*
  - *Requires changes to memory controllers*
  - *Knowledge of DRAM layout*

Google: Project Zero
Exploiting the DRAM rowhammer bug to gain kernel privileges
Mark Seaborn and Thomas Dullien

- March 2015

- Demonstrated using the Row Hammer failures as an exploit to gain kernel privileges

- Used CLFLUSH instruction

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Double Sided Hammering

- Increases bit flips in row n by hammering row n+1 and n-1
- Produced failures much faster
  - One machine had 25 bit flips in a single row using this technique
- Need to understand the physical geometry
  - Need to know physically adjacent row addresses
  - Was able to figure this out by hammering rows 256K below and above and observing increased bit flips

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Row Hammer Exploit #1

- Native Client Sandbox in Google Chrome escape
  - Uses the CLFLUSH instruction
  - Escape from the sandbox
  - Exploit works by triggering bit flips in the indirect jump instructions

Row Hammer Exploit #2

- Page Table Entry method
  - Use Row Hammer to flip bits in PTEs
  - Causes the PTE to point to another PTE
    - To increase probability of jumping to attacking code
      - Find bits that have failed and use them since they most likely will fail again
      - Spray Memory with page tables so if you jump you will most likely hit a PTE that points to attacking code

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Bit Flips in Laptops

- Google tested 29 laptops (without ECC)
  - 8 different models
  - 5 different memory vendors
  - Laptops ranged in date from 2010 to 2014
  - 15 of 29 laptops showed bit flips

Project Zero Summary

- Many bugs that appear to be difficult to exploit have turned out to be exploitable
  - The poisoned NUL byte, 2014 edition
    - a off-by-one NUL byte overwrite could be exploited to gain root privileges from a normal user account
  - Using Random bit flips: "Using Memory Errors to Attack a Virtual Machine" by Sudhakar Govindavajhala and Andrew W. Appel 2004

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Project Zero Summary

- Recommends disallowing the CLFLUSH for use in unprivileged code
  - Was removed from Google Chrome Native Client
- Points out several less likely methods that might succeed even without CLFLUSH
- Points at the need for more research especially using a JavaScript….this proves to be fortuitous….

Rowhammer.js: A Remote Software-Induced Fault Attack in JavaScript

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- Replaces CLFLUSH with a cache eviction strategy that gives a 99.99% successful eviction rate
- First remote software-induced hardware fault attack
  - Does not require physical access to the machine
  - Does not use native code or special instructions
- Via a web page can be performed on millions of users simultaneously without their knowledge
- Demonstration used Firefox v39 on a Linux machine

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Eviction Strategy

- Replaces the CLFLUSH instruction
- Uses large pages
  - Developed a tool to convert JavaScript array indices to physical addresses
  - This helps find the weak locations where the bit flips can be exploited
- Verified its eviction strategy for Sandy Bridge, Ivy Bridge and Haswell CPUs

Results

- JavaScript code performed as well as native code, but not as well as CLFLUSH
  - Haswell
    - No success unless the refresh rate was lowered
  - Ivy Bridge laptop
    - Produced significant bit flips

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Row Hammer Failures in Servers

- Third IO Mark Lanteigne
  - Memesis: A enterprise memory test
    - It is Linux Kernel Embedded, Lower Overhead and Is Closer to Hardware
    - Uses the e820 memory map and ACPI NUMA for precise memory targeting
    - HPC Parallel Processing – uses the full power of all CPU cores
    - Provides higher DRAM bandwidth versus the Stream benchmark (verified)

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Row Hammer Failures resulting in Machine Checks

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ECC Systems are Vulnerable

- Third I/O often encounters ECC protected servers that can be extremely vulnerable to Row Hammer
- Even after 2X refresh mitigation in place
- ECC errors (with thresholding, means hundreds of errors before first reporting)
- CMCI Storms (too many ECC errors reported)
  - ECC is broken! No reporting standards
- Performance problems, reboots, lockups, halts

ThirdIO Contact Information

- Mark Lanteigne
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Row Hammer Software

- Passmark MemTest86 Test 13
- Github: Mark Seaborn's code
  - https://github.com/google/rowhammer-test
- Github: CMU code
  - https://github.com/CMU-SAFARI/rowhammer
- Github: Rowhammer.js
  - https://github.com/IAIK/rowhammerjs
- ThirdIO: Memesis for Servers

Testing the system for excessive ACTIVATE commands

- Repurposed our DDR Detective® Protocol Analyzer to count ACT commands to unique Row Addresses (Row Hammer feature)

Running the Google code

ECC helps but will not prevent undetected data corruption

- Error Correction Codes on DDR3 are Single Error Detection and Correction and Double Error Detection

- Research showed more than 2 bits on a single 64 bit access
  - However the rate of failures was much less

- Multibit errors will not be detected or erroneously flagged as SEDC

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Mitigation Strategies

- Row Activate Counters: Counts Activates to Rows and issues dummy ACT to neighboring Rows
  - Requires significant changes the memory controller/DRAM
- Probabilistic Row Activation (CMU): Memory controller issues dummy ACT commands to neighboring Rows
  - Requires changes to the memory controller and knowledge of the DRAM layout
- Targeted Row Refresh
  - Requires special DRAM and changes to memory controller
- Double the Refresh Rate
  - **Best Solution for existing hardware:** Performance and power penalty

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Row Hammer failures on DDR4?

Rowhammer mitigation

My i7-5820K/GA-X99-UD4/2400MHz Crucial Ballistix DDR4 system was failing rowhammer (a few hundred errors per pass) until I reduced the refresh interval timing from the default of 7.8ms, in spite of the fact that DDR4 is supposed to include rowhammer mitigation (source: https://en.wikipedia.org /wiki/Row_hammer#Mitigation)

In my board's BIOS, the two settings were tREFI (default of 9360) and tREFIX9 (default of 82).

refresh interval (ms) = tREFI / (RAM clock (MHz) / 2)

tREFIX9 = 8.9 * tREFI / 1024

so...

9360/(2400/2)=7.8ms

(Source: page 123 of http://www.intel.com/content/dam/www...-datasheet.pdf)

The standard recommendation is to reduce the refresh interval to 3.9ms and thereby double the refresh rate (source: http://support.lenovo.com/us/en/prod...ity/row_hammer). Doing that gave me one error per pass at the same address both times, so I reduced the interval to 75% of 3.9ms (i.e. tREFI=3510, tREFIX9=31) and it's now error free over 8 passes overnight.
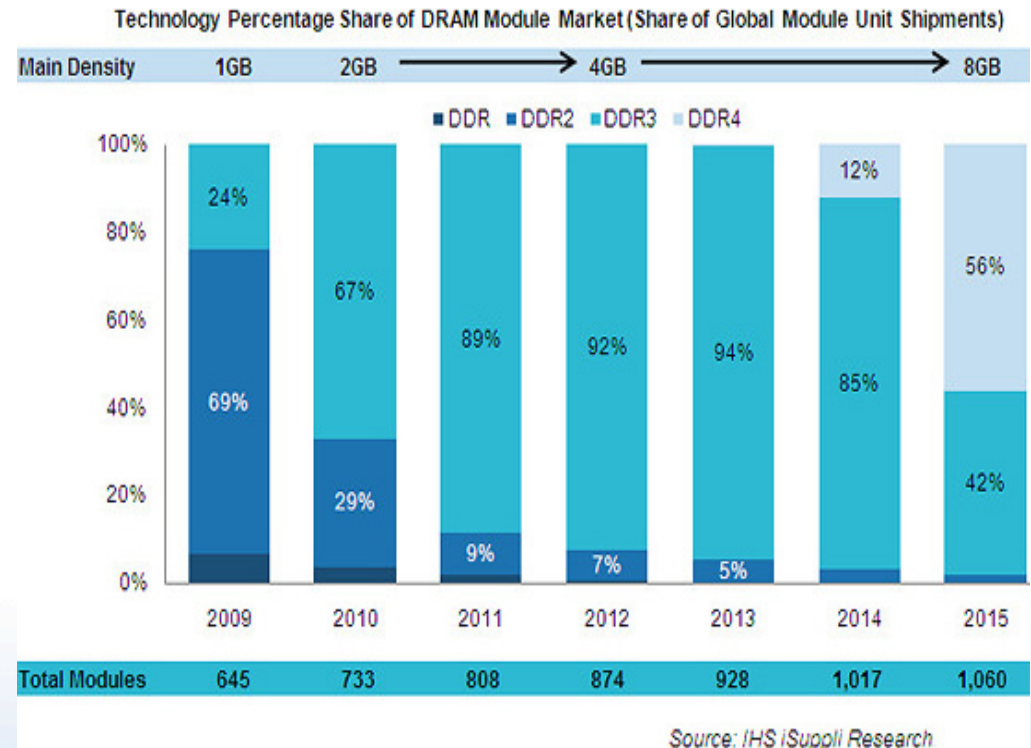
Passmark Blog

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Summary

- DDR3 Memory is everywhere!

- Critical Applications need to be aware of this issue

  – Its both a reliability issue and a security issue

- ECC protected memory should be used but is not a fix for this problem

Technology Percentage Share of DRAM Module Market (Share of Global Module Unit Shipments)

Main Density	1GB	2GB	4GB				8GB

■DDR ■DDR2 ■DDR3 ■DDR4

Total Modules	645	733	808	874	928	1,017	1,060

Source: IHS iSuppli Research

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